

DESCRIPTION

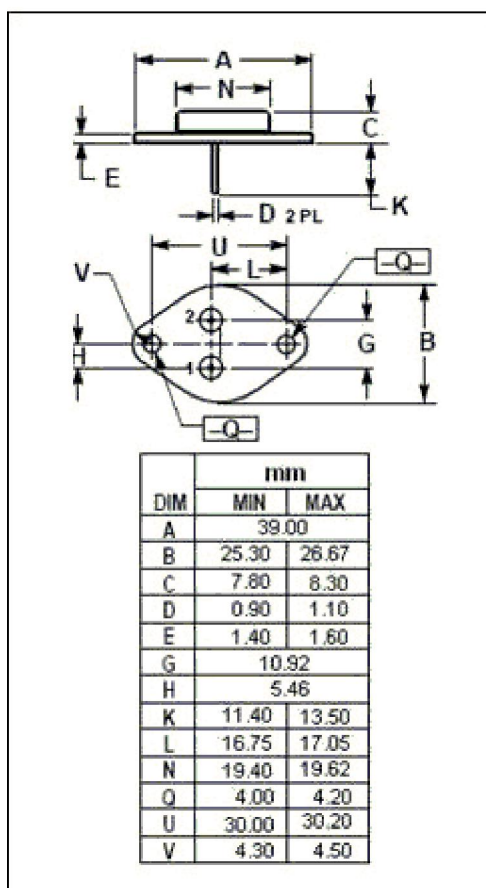
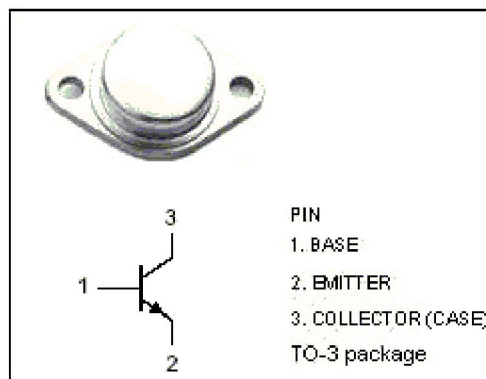
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 200V(\text{Min.})$
- DC Current Gain-
: $h_{FE} = 30 \sim 250(\text{Min.}) @ I_C = 0.5A$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 2.0V(\text{Max}) @ I_C = 1A$

APPLICATIONS

- Designed for switching regulator and power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	3	A
P_C	Collector Power Dissipation@ $T_C = 25^\circ\text{C}$	50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



SPTECH Silicon NPN Power Transistor**3DD208****ELECTRICAL CHARACTERISTICS** **$T_C=25^{\circ}\text{C}$ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; I_B=0$	200		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=5\text{mA}; I_E=0$	300		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	6		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.1\text{A}$		2.0	V
I_{CEO}	Collector Cutoff Current	$V_{CE}=50\text{V}; I_B=0$		0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$		0.1	mA
h_{FE}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=10\text{V}$	30	250	